

Supplementary Materials for Self-Rectifying Resistive Switching and Short-Term Memory Characteristics in Pt/HfO₂/TaO_x/TiN Artificial Synaptic Device

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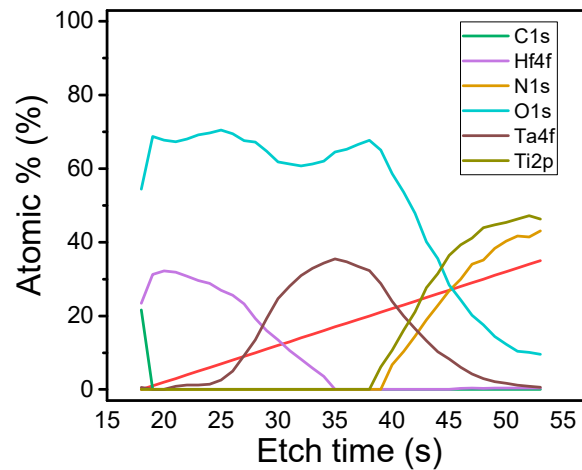


Figure S1. XPS atomic % depth profile of HfO₂/TaO_x/TiN device.

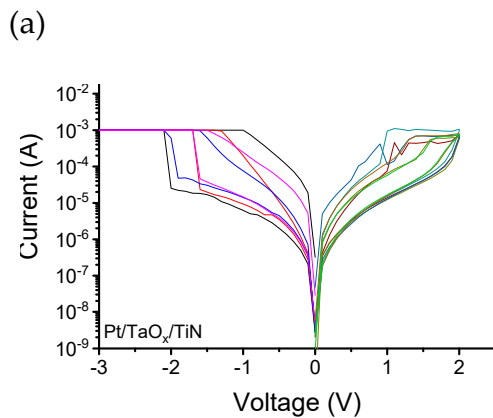


Figure S2. I-V curves of (a) Pt/TaO_x/TiN device and (b) Pt/HfO₂/TiN devices.